

## JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

# **SOT-89-3L Plastic-Encapsulate Transistors**

# **A92** TRANSISTOR (PNP)

## **FEATURES**

- Low Collector-Emitter Saturation Voltage
- High Breakdown Voltage

# 1. BASE 2. COLLECTOR 3. EMITTER

SOT-89-3L

### **MARKING: A92**

## MAXIMUM RATINGS (T<sub>a</sub>=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	-310	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-305	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
Ic	Collector Current- Continuous	-200	mA
I <sub>CA</sub>	Collector Current -Pulsed	-500	mA
Pc	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	250	°C/W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C

## **ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25℃ unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μA,I <sub>E</sub> =0	-310			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA,I <sub>B</sub> =0	-305			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-100μA,I <sub>C</sub> =0	-5			V
	I <sub>CBO</sub>	V <sub>CB</sub> =-200V,I <sub>E</sub> =0			-0.25	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> =-200V,I <sub>B</sub> =0			-0.25	μA
		V <sub>CE</sub> =-300V,I <sub>B</sub> =0			-5	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V,I <sub>C</sub> =0			-0.1	μA
	h <sub>FE(1)</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-1mA	60			
DC current gain	h <sub>FE(2)</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-10mA	100		300	
	h <sub>FE(3)</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-80mA	60			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-20mA,I <sub>B</sub> =-2mA			-0.2	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-20mA,I <sub>B</sub> =-2mA			-0.9	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-20V,I <sub>C</sub> =-10mA,f=30MHz	50			MHz

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